

HTD2A80AS

2A TRIAC

FEATURES

- ❑ Repetitive Peak Off-State Voltage : 1000V
- ❑ R.M.S On-State Current ($I_{T(RMS)} = 2A$)
- ❑ Gate Trigger Current : 10mA
- ❑ $dV/dt \geq 500V/\mu s$
- ❑ High Voltage Blocking Capability

General Description

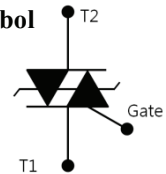
Intended for use in AC static switching and industrial control systems, driving low power highly inductive load like solenoid, pump, fan ad micro-motor.

$$V_{DRM} = 1000 V$$

$$I_{T(RMS)} = 2 A$$

$$I_{TSM} = 17 A$$

$$I_{GT} = 10mA$$

Symbol

D-PAK


1. T1 2. T2 3. G

Absolute Maximum Ratings ($T_J=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DRM}	Repetitive Peak Off-State Voltage	Sine wave, 50/60Hz, Gate open	1000	V
V_{RRM}	Repetitive Peak Reverse Voltage		1000	V
V_{DSM}	Non-Repetitive Surge Peak Off-State Voltage		1100	V
V_{RSM}	Non-Repetitive Peak Reverse Voltage		1100	V
$I_{T(RMS)}$	R.M.S. On-State Current	Full sine wave, $T_C = 95^\circ C$	2	A
I_{TSM}	Non-Repetitive Surge Peak On-State Current	Full sine wave, 50Hz/60Hz	16/17	A
I^2t	Fusing Current	$t = 10ms$	1.28	A ² S
P_{GM}	Forward Peak Gate Power Dissipation	$T_J = 80^\circ C$	1	W
$P_{G(AV)}$	Forward Average Gate Power Dissipation	$T_J = 80^\circ C$	0.2	W
I_{GM}	Peak Gate Current	$tp \leq 2\mu s, T_J = 80^\circ C$	1	A
T_J	Operating Junction Temperature		-40~+125	$^\circ C$
T_{STG}	Storage Temperature		-40~+150	$^\circ C$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
I_{DRM}	Repetitive Peak Off-State Current	$V_D = V_{\text{DRM}}$	$T_J=25^\circ\text{C}$	-	-	10	μA
			$T_J=125^\circ\text{C}$	-	-	500	μA
I_{RRM}	Repetitive Peak Reverse Current	$V_R = V_{\text{RRM}}$	$T_J=25^\circ\text{C}$	-	-	10	μA
			$T_J=125^\circ\text{C}$	-	-	500	μA
I_{GT}	Gate Trigger Current	$V_D = 12\text{V}, R_L=30\Omega$	1+	-	-	6	mA
			1-, 3-	-	-	10	mA
V_{GT}	Gate Trigger Voltage	$V_D = 12\text{V}, R_L=30\Omega$	1+, 1-, 3-	-	-	1.5	V
V_{GD}	Non-Trigger Gate Voltage	$V_D = 2/3 V_{\text{DRM}}, R_L=3.3\text{K}\Omega,$ $T_J=125^\circ\text{C}$	0.2	-	-	V	
I_L	Latching Current	$I_G = 1.2 I_{\text{GT}}$	1+, 3-	-	-	15	mA
			1-	-	-	25	mA
I_H	Holding Current	$I_T = 100\text{mA}$	-	-	10	mA	
V_{TM}	Peak On-State Voltage	$I_T = 2\text{A}, t_p = 380\mu\text{s}$	-	-	1.6	V	
dv/dt	Critical Rate of Rise of Off-State Voltage	$V_D = 2/3 V_{\text{DRM}},$ Gate open, $T_J=125^\circ\text{C}$	500	-	-	V/us	

Thermal Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{\theta\text{JC}}$	Thermal Resistance	Junction to Case			4.5	$^\circ\text{C/W}$

Typical Characteristics

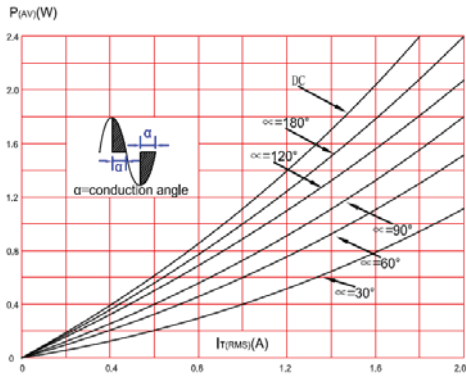


Fig 1. R.M.S. current vs. Power dissipation

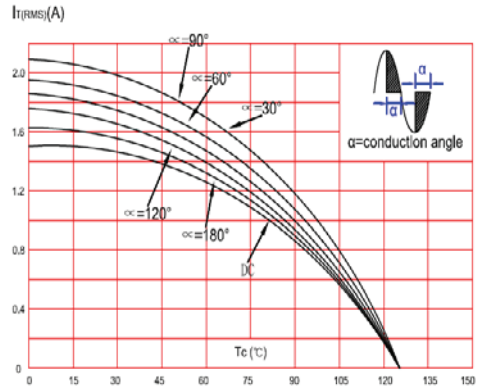


Fig 2. R.M.S. current vs. Case temperature

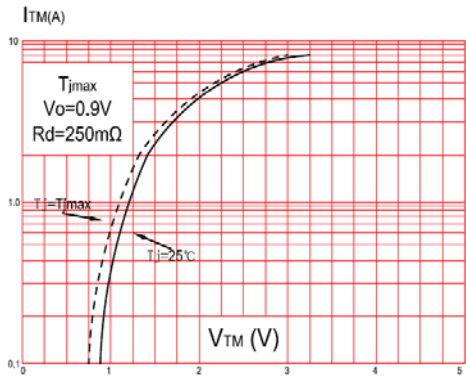


Fig 3. Surge on state characteristics

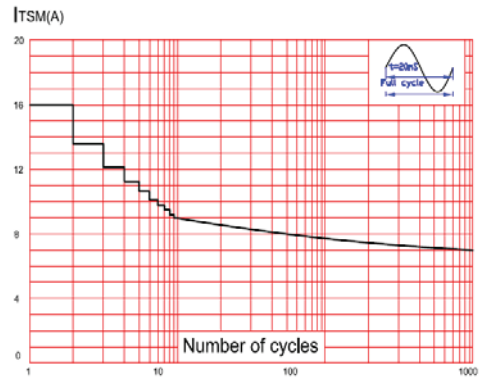


Fig 4. Surge on state current rating

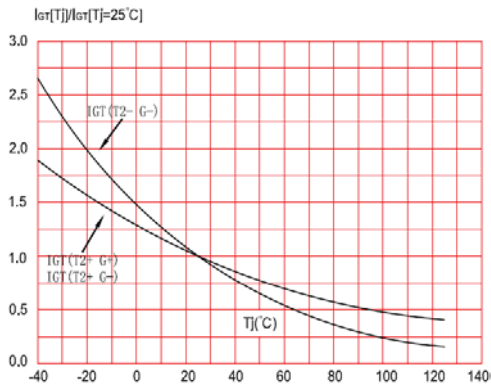


Fig 5. Gate trigger current vs. junction temperature

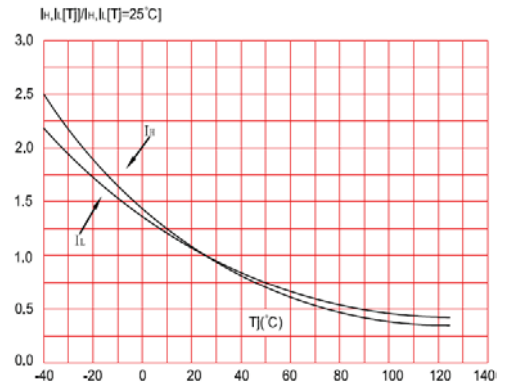
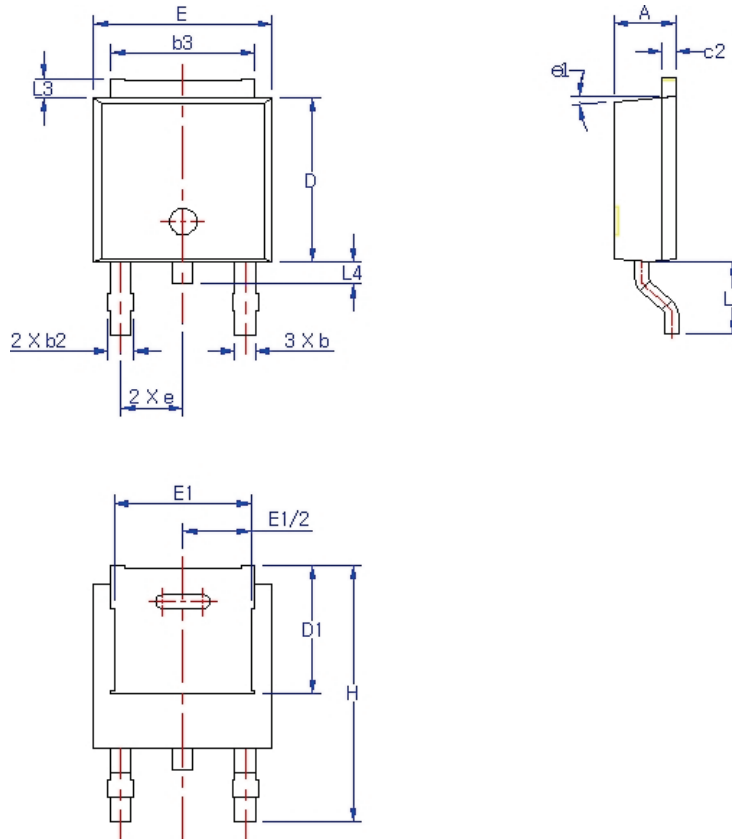


Fig 6. Holding and latching current vs. junction temperature

Package Dimension

TO-252



SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1 (▼)	0.00	-	0.127
b	0.66	0.76	0.86
b2	-	-	0.96
b3	5.04	5.34	5.64
c2	0.40	0.50	0.60
D	5.90	6.10	6.30
D1	(4.75)		
E	6.40	6.60	6.80
E1	(5.04)		
e	2.30 BSC		
H	9.20	9.50	9.80
L	1.27	1.47	1.67
L1	2.50	2.70	2.90
L2	0.508 BSC		
L3	0.50	0.70	0.90
L4	0.60	0.80	1.00
e	0°	-	10°
e1	(5°)		